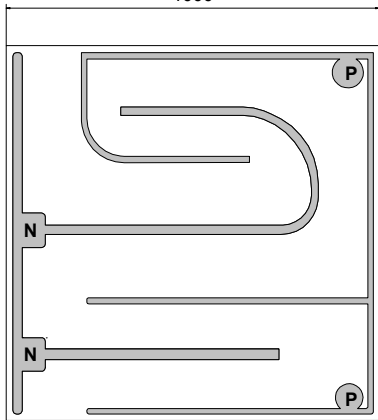


Radiation	Type	Technology	Electrodes
Green	Standard	InGaN/Al ₂ O ₃	Both on top side

	typ. dimensions (± 25) μm
	<u>typ. thickness</u> 90 (± 10) μm <u>contact metalization</u> gold alloy, 1.5 μm <u>backside metalization</u> aluminium alloy, 1.0 μm

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		2.5	3.1	V
Forward voltage ¹⁾	$I_F = 350 \text{ mA}$	V_F		3.19	3.7	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Luminous intensity ¹⁾	$I_F = 20 \text{ mA}$	I_V	1300	1500		mcd
Luminous intensity ¹⁾	$I_F = 350 \text{ mA}$	I_V	12000	14000		mcd
Peak wavelength	$I_F = 20 \text{ mA}$	λ_P		524		nm
Dominant wavelength	$I_F = 350 \text{ mA}$	λ_D	515	525	535	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		35		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		10		ns

¹⁾Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$I_V(\text{typ})$ [mcd]	$V_F(\text{typ})$ [V]	Quantity
ELC-525-31				

Packing: Chips on adhesive film with wire-bond side on top